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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-8EWH06FNTRHM3</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of VS-8EWH06FNTRHM3 - DIODE HYPERFAST 8A DPAK

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VS-8EWH06FNHM3

Vishay Semiconductors

HALOGEN

FREE

Hyperfast Rectifier, 8 A FRED Pt®



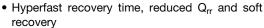


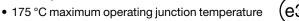
TO-252AA (D-PAK)

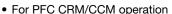
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0 1	3 O
N/C	Anode

PRODUCT SUMMARY				
Package	TO-252AA (D-PAK)			
I _{F(AV)}	8 A			
V_{R}	600 V			
V _F at I _F	1.3 V			
t _{rr} (typ.)	18 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES







Low forward voltage drop

Low leakage current

AEC-Q101 qualified

• Meets JESD 201 class 2 whisker test

• Meets MSL level 1, per J-STD-020, LF maximum peak

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 143 °C	8		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	90	Α	
Peak repetitive forward current	I _{FM}	T _C = 143 °C, f = 20 kHz, d = 50 %	16		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
Forward voltage	V _F	I _F = 8 A	-	2.0	2.4	V
Forward voltage	VF	I _F = 8 A, T _J = 150 °C	-	1.3	1.8	
Deverse leakage current	1	$V_R = V_R$ rated	-	-	50	
Reverse leakage current I _R		T _J = 150 °C, V _R = V _R rated	-	-	500	μA
Junction capacitance	C _T	V _R = 600 V	-	8	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH

Revision: 10-Jul-15 Document Number: 94739



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50$	I _F = 1 A, dI _F /dt = 50 A/μs, V _R = 30 V		21		
Reverse recovery time t_{rr}		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A/}\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	18	22	
	L _{rr}	T _J = 25 °C		-	25	-	ns
		T _J = 125 °C		-	34	-	
Peak recovery current I _{RRM}	1	T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	3.3	-	A
	'RRM	T _J = 125 °C		-	4.8	-	_ ^
Reverse recovery charge	0	T _J = 25 °C		-	39	-	nC
	Q _{rr}	T _J = 125 °C		-	90	-	I IIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.8	2.2	°C/W
Approximate weight				0.3		g
Approximate weight				0.01		oz.
Marking device		Case style TO-252AA (D-PAK)		8EWH	06FNH	

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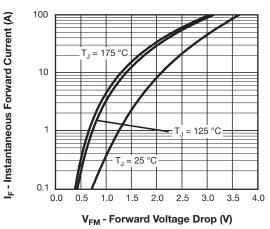


Fig. 1 - Typical Forward Voltage Drop Characteristics

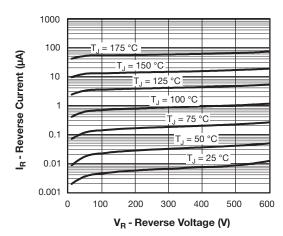


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

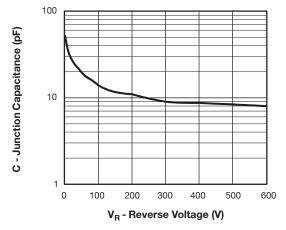


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

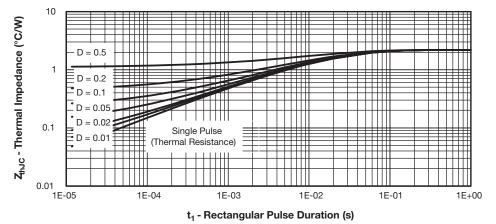


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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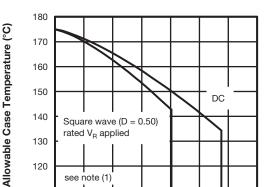
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I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

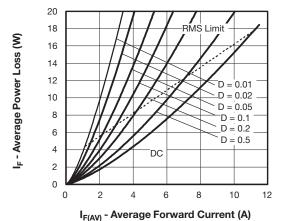


Fig. 6 - Forward Power Loss Characteristics

35 30 25 20 15 10 100 100 1000 1000

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

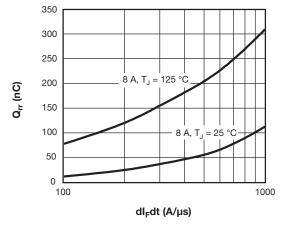


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \ x \ V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ \text{at} \ V_{R1} = \text{Rated} \ V_R \\ \end{array}$

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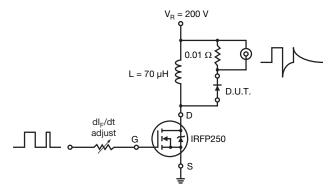
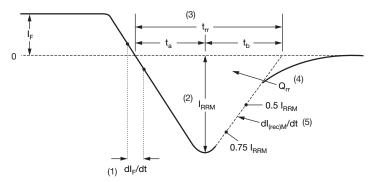


Fig. 9 - Reverse Recovery Parameter Test Circuit



- dl_F/dt rate of change of current through zero crossing
- (2) $\rm I_{RRM}$ peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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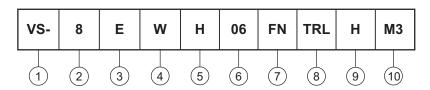


VS-8EWH06FNHM3

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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (8 = 8 A)

Circuit configuration:

E = single diode

Package identifier:

W = D-PAK

5 - H = hyperfast recovery

6 - Voltage rating (06 = 600 V)

- FN = TO-252AA

8 - • None = tube

TR = tape and reel

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-8EWH06FNHM3	75	3000	Antistatic plastic tube	
VS-8EWH06FNTRHM3	2000	2000	13" diameter reel	
VS-8EWH06FNTRRHM3	3000	3000	13" diameter reel	
VS-8EWH06FNTRLHM3	3000	3000	13" diameter reel	

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95519		
Part marking information	www.vishay.com/doc?95518		
Packaging information	www.vishay.com/doc?95033		

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